

Mi-Hee Ji

List of Publications by Year in descending order

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papers

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840776

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docs citations

22
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811
citing authors

#	ARTICLE	IF	CITATIONS
1	Demonstration of Large-Size Vertical Ga ₂ O ₃ Schottky Barrier Diodes. IEEE Transactions on Power Electronics, 2021, 36, 41-44.	7.9	38
2	Direct metal contacts printing on 4H-SiC for alpha detectors and inhomogeneous Schottky barriers. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 989, 164961.	1.6	4
3	Flexible single-crystalline GaN substrate by direct deposition of III-N thin films on polycrystalline metal tape. Journal of Materials Chemistry C, 2021, 9, 2243-2251.	5.5	6
4	Large area vertical Ga ₂ O ₃ Schottky diodes for X-ray detection. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 1013, 165664.	1.6	4
5	Thermal and radiation response of 4H-SiC Schottky diodes with direct-write electrical contacts. Applied Physics Letters, 2020, 116, .	3.3	9
6	Temperature-Dependent Leakage Current Characteristics of Homojunction GaN p-i-n Rectifiers Using Ion-Implantation Isolation. IEEE Transactions on Electron Devices, 2019, 66, 4273-4278.	3.0	15
7	Structural and Electrical Characterization of Ammonothermal Free-Standing GaN Wafers. Progress toward Pilot Production. Materials, 2019, 12, 1925.	2.9	10
8	Demonstration of uniform and reliable GaN p-i-p-i-n separate-absorption and multiplication ultraviolet avalanche photodiode arrays with large detection area. , 2019, , .		3
9	p-i-p-i-n Separate Absorption and Multiplication Ultraviolet Avalanche Photodiodes. IEEE Photonics Technology Letters, 2018, 30, 181-184.	2.5	23
10	Raman Scattering Study of Lattice Vibrations in the Type-II Superlattice $\text{InAs}_{1-x}\text{Sb}_x$ Physical Review Applied, 2017, 8, .	3.8	7
11	Rethinking phonons: The issue of disorder. Npj Computational Materials, 2017, 3, .	8.7	66
12	Effect of lattice-matched InAlGa _n electron-blocking layer on hole transport and distribution in InGa _n /Ga _n multiple quantum wells of visible light-emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1296-1301.	1.8	3
13	Uniform and Reliable GaN p-i-n Ultraviolet Avalanche Photodiode Arrays. IEEE Photonics Technology Letters, 2016, 28, 2015-2018.	2.5	26
14	Effect of Group-III precursors on unintentional gallium incorporation during epitaxial growth of InAlN layers by metalorganic chemical vapor deposition. Journal of Applied Physics, 2015, 118, .	2.5	5
15	Al _x Ga _{1-x} N Ultraviolet Avalanche Photodiodes With Avalanche Gain Greater Than 10^5 . IEEE Photonics Technology Letters, 2015, 27, 642-645.	2.5	38
16	Comparison of AlGa _n ultraviolet avalanche photodiodes grown on free-standing GaN and sapphire substrates. Applied Physics Express, 2015, 8, 122202.	2.4	23
17	GaN/InGa _n avalanche phototransistors. Applied Physics Express, 2015, 8, 032101.	2.4	20
18	Temperature-Dependent Characteristics of GaN Homojunction Rectifiers. IEEE Transactions on Electron Devices, 2015, 62, 2679-2683.	3.0	19

#	ARTICLE	IF	CITATIONS
19	Direct periodic patterning of GaN-based light-emitting diodes by three-beam interference laser ablation. Applied Physics Letters, 2014, 104, 141105.	3.3	9
20	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. Journal of Crystal Growth, 2014, 388, 143-149.	1.5	44
21	Improved Hole Transport by $\text{In}_{1-x}\text{Ga}_x\text{N}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.	2.5	2
22	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	3.3	80